

# TIP110, TIP115



## Darlington Transistors



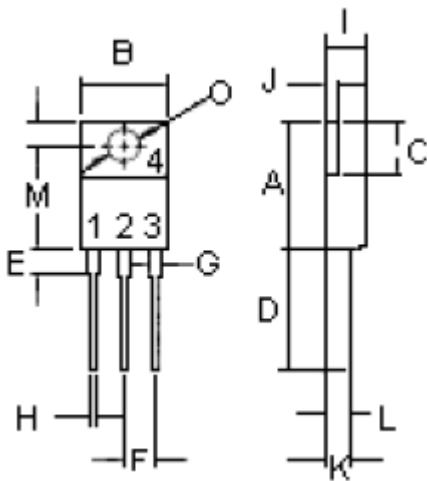
### Features:

- Collector - emitter sustaining voltage -  $V_{CEO(sus)} = 60\text{ V}$  (minimum)
- Collector - emitter saturation voltage -  $V_{CE(sat)} = 2.5\text{ V}$  (maximum) at  $I_C = 2\text{ A}$
- Monolithic construction with built-in-base-emitter shunt resistor

### Application:

Designed for general-purpose amplifier and low speed switching applications

TO - 220



Dimensions	Minimum	Maximum
A	14.68	15.31
B	9.78	10.42
C	5.01	6.52
D	13.06	14.62
E	3.57	4.07
F	2.42	3.66
G	1.12	1.36
H	0.72	0.96
I	4.22	4.98
J	1.14	1.38
K	2.2	2.97
L	0.33	0.55
M	2.48	2.98
O	3.7	3.9

Dimensions : Millimetres

### Pin

1. Base
2. Collector
3. Emitter
4. Collector (Case)

### Maximum Ratings

Characteristic	Symbol	TIP110 TIP115	Unit
Collector - emitter voltage	$V_{CEO}$	60	V
Collector - base voltage	$V_{CBO}$	60	V
Emitter - base voltage	$V_{EBO}$	5	V
Collector current - Continuous	$I_C$	2	A
- Peak	$I_{CM}$	4	
Base current	$I_B$	50	mA
Total power dissipation at $T_c = 25^\circ\text{C}$	$P_D$	50	W
derate above $25^\circ\text{C}$		0.4	W/ $^\circ\text{C}$
Operating and storage Junction temperature range	$T_J, T_{STG}$	-65 to +150	$^\circ\text{C}$

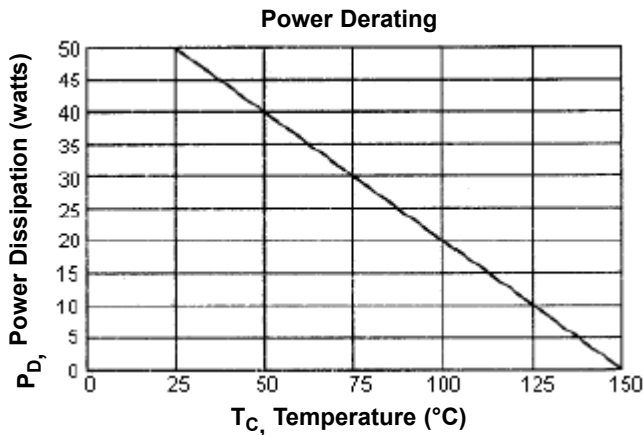


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### Thermal Characteristics

Characteristic	Symbol	Maximum	Unit
Thermal resistance junction to case	$R_{\theta jc}$	2.5	$^{\circ}\text{C/W}$



### Electrical Characteristics ( $T_C = 25^{\circ}\text{C}$ Unless Otherwise noted)

Characteristics	Symbol	Minimum	Maximum	Units
<b>Off Characteristics</b>				
Collector - emitter sustaining voltage (1) ( $I_C = 30\text{ mA}$ , $I_B = 0$ )	$V_{CEO(\text{SUS})}$	60	-	V
Collector cut off current ( $V_{CE} = 30\text{ V}$ , $I_B = 0$ )	$I_{CEO}$	-	2	mA
Collector cut off current ( $V_{CB} = 60\text{ V}$ , $I_E = 0$ )	$I_{CBO}$	-	1	mA
Emitter cut off current ( $V_{EB} = 5\text{ V}$ , $I_C = 0$ )	$I_{EBO}$	-	2	mA
<b>On Characteristics (1)</b>				
DC current gain ( $I_C = 1\text{ A}$ ; $V_{CE} = 4\text{ V}$ ) ( $I_C = 2\text{ A}$ ; $V_{CE} = 4\text{ V}$ )	$h_{FE}$	1,000 500	-	-
Collector - emitter saturation voltage ( $I_C = 2\text{ A}$ ; $I_B = 8\text{ mA}$ )	$V_{CE(\text{sat})}$	-	2.5	V
Base-emitter on voltage ( $I_C = 2\text{ A}$ ; $V_{CE} = 4\text{ V}$ )	$V_{BE(\text{on})}$	-	2.8	V
<b>Dynamic characteristics</b>				
Small signal current gain ( $I_C = 0.75\text{ A}$ ; $V_{CE} = 10\text{ V}$ , $f = 1\text{ MHz}$ )	$h_{fe}$	25	-	-
Output capacitance ( $V_{CB} = 10\text{ V}$ ; $I_E = 0$ , $f = 0.1\text{ MHz}$ )	$C_{ob}$	-	250 150	pF

(1) Pulse test: Pulse width = 300  $\mu\text{s}$ , duty cycle  $\leq 2\%$

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### Internal Schematic Diagram

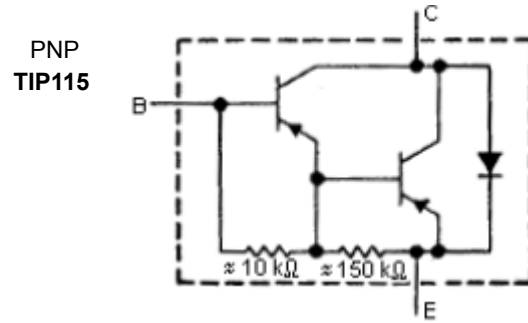
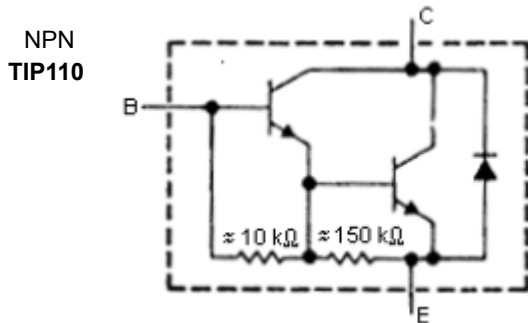


Figure-2 Switching Time

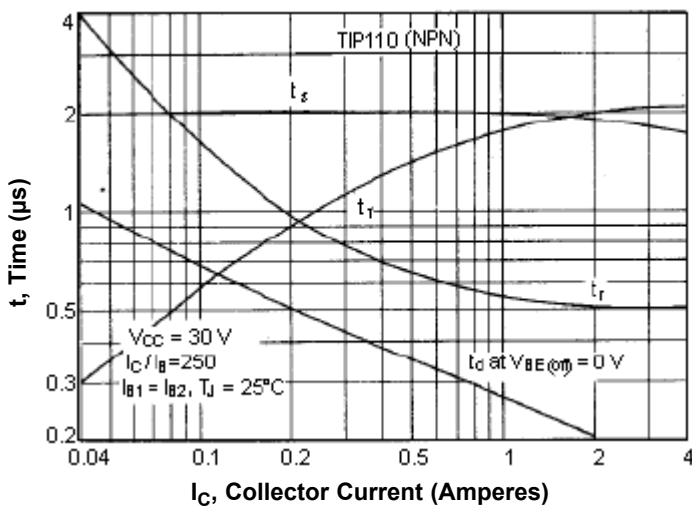


Figure-3 Switching Time

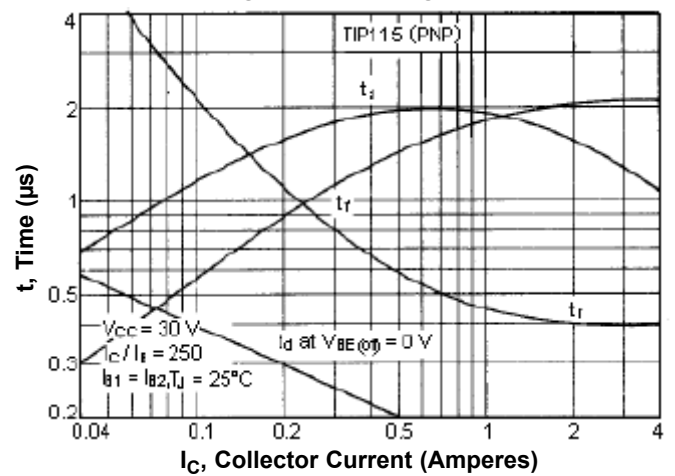


Figure-4 Capacitances

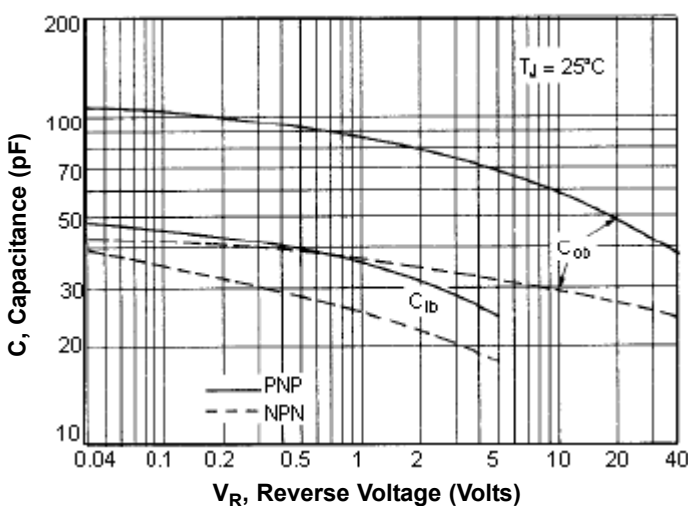
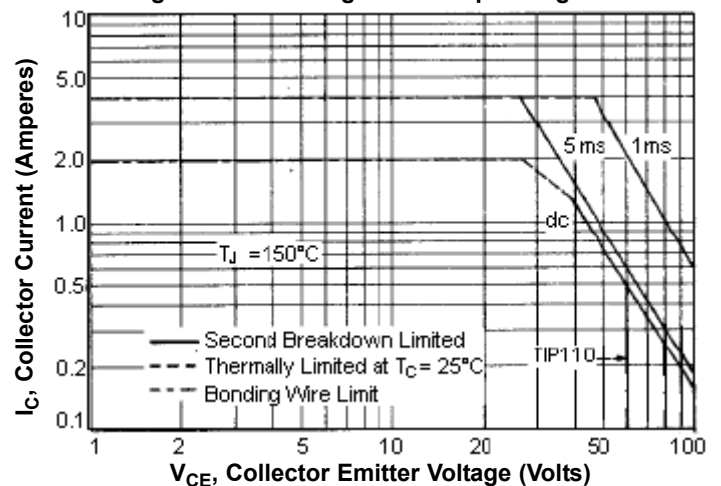


Figure-5 Active Region Safe Operating Area

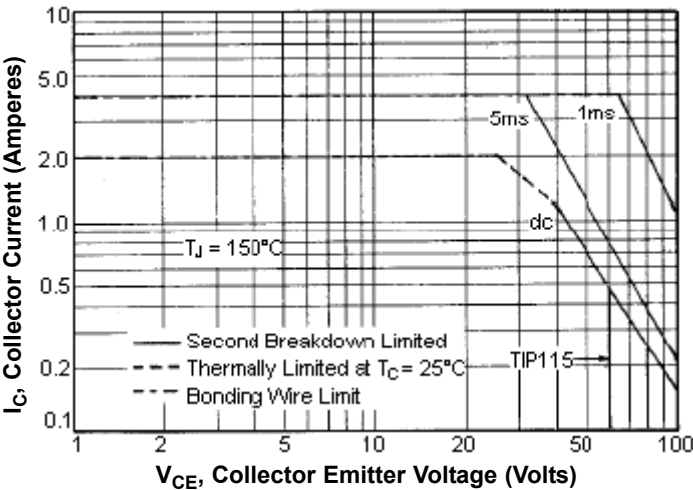


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Figure-6 Active Region Safe Operating Area



There are two limitation on the power handling ability of a transistor: average junction temperature and second breakdown safe operating area curves indicate  $I_C$ - $V_{CE}$  limits of the transistor that must be observed for reliable operation i.e., the transistor must not be subjected to greater dissipation than the curves indicate

The data of Figure - 5 and 6 is base on  $T_{J(PK)} = 150^{\circ}\text{C}$ ;  $T_C$  is variable depending on power level. Second breakdown pulse limits are valid for duty cycles to 10% provided  $T_{J(PK)} \leq 150^{\circ}\text{C}$ . At high case temperatures, thermal limitation will reduce the power that can be handled to values less than the limitations imposed by second breakdown

### Specifications Table

Description	$I_C$ (av) maximum (A)	$V_{CE0}$ maximum V	$h_{FE}$ minimum at $I_C = 1\text{ A}$	$P_{tot}$ at $25^{\circ}\text{C}$ (W)	Type	Part Number
Darlington Transistors	2	60	1,000	50	NPN	TIP110
					PNP	TIP115

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